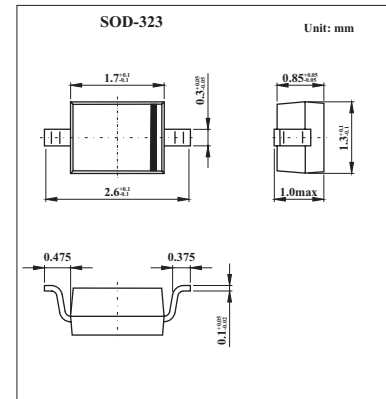


## Silicon PIN Diode

## BA595

## ■ Features

- Current-controlled RF resistor for switching and attenuating applications
- Frequency range 1 MHz ... 2 GHz
- Especially useful as antenna switch in TV-sat tuners
- Very low harmonics

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	50	V
Forward current	$I_F$	50	mA
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-55 to +125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 370$	K/W

Note

1. For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 30\text{ V}$			20	nA
Forward voltage	$V_F$	$I_F = 50\text{ mA}$			1.1	V
Diode capacitance	$C_T$	$V_R = 0\text{ V}, f = 100\text{ MHz}$		0.26	0.4	pF
		$V_R = 10\text{ V}, f = 1\text{ MHz}$		0.22	0.6	
Reverse parallel resistance	$R_P$	$V_R = 1\text{ V}, f = 100\text{ MHz}$		50		K $\Omega$
		$V_R = 0\text{ V}, f = 1\text{ GHz}$		10		
Forward resistance	$r_f$	$I_F = 1.5\text{ mA}, f = 100\text{ MHz}$		22	40	$\Omega$
		$I_F = 10\text{ mA}, f = 100\text{ MHz}$		4.5	7	
Charge carrier life time	$\tau_{rr}$	$I_F = 10\text{ mA}, I_R = 6\text{ mA}$ , measured at $I_R = 3\text{ mA}, R_L = 100\ \Omega$		1600		ns
I-region width	$W_I$			130		$\mu\text{ m}$

## ■ Marking

Marking	R
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